



FZT788B

#### 15V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

#### **Features**

- $BV_{CEO} > -15V$
- $BV_{CBO} > -15V$
- I<sub>C</sub> = -3A High Continuous Current
- h<sub>FE</sub> > 300 @ -2A and Low Saturation Voltage
- Extremely Low Equivalent On-Resistance R<sub>CE(sat)</sub> 93mΩ at -3A
- Complementary NPN Type: FZT688B
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

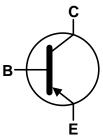
### **Applications**

- Flash Gun Convertors
- **Battery Powered Circuits**

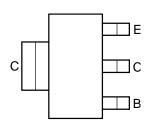
SOT223



Top View



Device Symbol



Top View Pin-Out

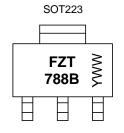
#### Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT788BTA	AEC-Q101	FZT788B	7	12	1,000
FZT788BTC	AEC-Q101	FZT788B	13	12	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



FZT 788B = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W = Week Code (01~53)$ 



#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-15	V
Collector-Emitter Voltage	$V_{CEO}$	-15	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I <sub>CM</sub>	-8	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3		
Dower Discipation	(Note 6)	Б	2	W	
Power Dissipation	(Note 7)	P <sub>D</sub>	1.6		
	(Note 8)		1.2	]	
	(Note 5)		41.7	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)		62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1		
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

### ESD Ratings (Note 10)

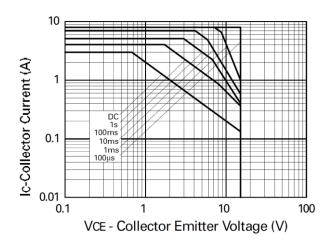
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

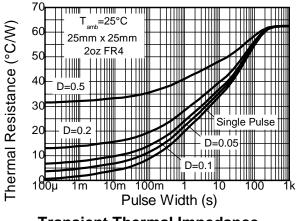
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



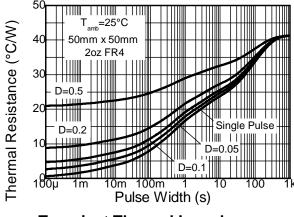
# Thermal Characteristics and Derating Information



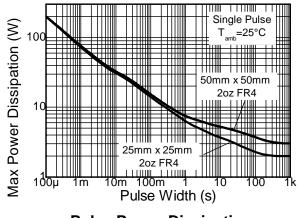
### Safe Operating Area



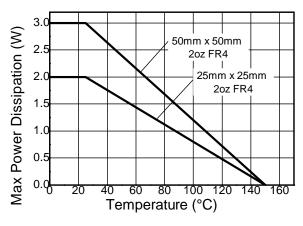
Transient Thermal Impedance



**Transient Thermal Impedance** 







**Derating Curve** 



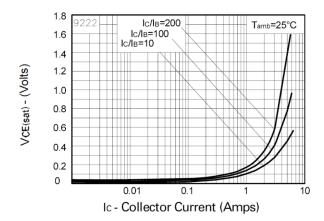
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-15	_	_	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-15	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	I <sub>E</sub> = -100μA
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	_	-100	nA	V <sub>CB</sub> = -10V
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	-100	nA	V <sub>EB</sub> = -4V
DC Current Gain (Note 11)	h <sub>FE</sub>	500 400 300 150	_ _ _ _	_ _ _ _	_	$I_{C} = -10$ mA, $V_{CE} = -2$ V $I_{C} = -1$ A, $V_{CE} = -2$ V $I_{C} = -2$ A, $V_{CE} = -2$ V $I_{C} = -6$ A, $V_{CE} = -2$ V
Collector-Emitter Saturation Voltage (Note 11)	VCE(sat)	_ _ _	_ _ _ _	-0.15 -0.25 -0.45 -0.5	V	$I_C = -0.5A$ , $I_B = -2.5mA$ $I_C = -1A$ , $I_B = -5mA$ $I_C = -2A$ , $I_B = -10mA$ $I_C = -3A$ , $I_B = -50mA$
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	_	-0.9	V	$I_C = -1A, I_B = -5mA$
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	-0.75	_	V	I <sub>C</sub> = -1A, V <sub>CE</sub> = -2V
Input Capacitance	C <sub>ibo</sub>	_	225	_	pF	V <sub>EB</sub> = -0.5V, f = 1MHz
Output Capacitance	C <sub>obo</sub>	_	25	_	pF	V <sub>CB</sub> = -10V, f = 1MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	_	_	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -50mA, f=50MHz
Turn-On Time	t <sub>on</sub>	_	35	_	ns	V <sub>CC</sub> = -10V, I <sub>C</sub> = -500mA
Turn-Off Time	t <sub>off</sub>		400		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

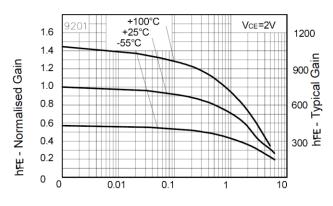
Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

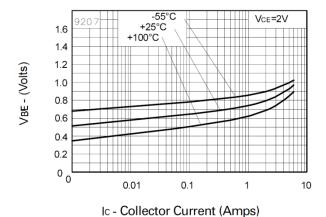


#### VCE(sat) v IC

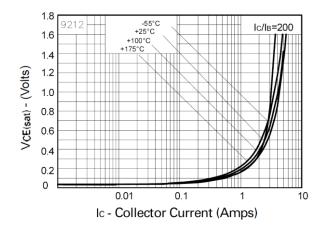


Ic - Collector Current (Amps)

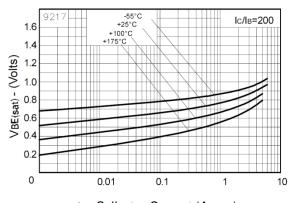
#### hFE v IC



VBE(on) v IC



VCE(sat) v IC



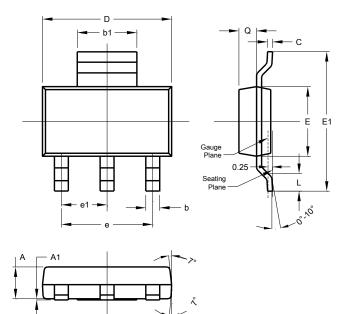
Ic - Collector Current (Amps)

VBE(sat) v IC



### **Package Outline Dimensions**

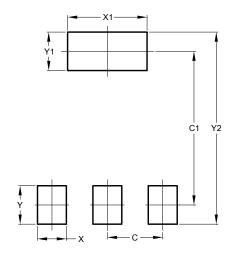
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [	All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8 00



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